

Day 1 - September 25, 2017			Day 2 - September 26, 2017			Day 3 - September 27, 2017		
08.45am	Registration		8.45am	Registration		8.45am	Registration	
09.15am	Workshop opening (ARCSIS and CMP)							
9.30 am	Keynote speaker	Betty Prince, CEO, Memory Strategies International (USA) - "Embedded Non-Volatile Memories for Intelligent IoT"	09.00 am	Day 2		09.00 am	Day 3	
Session 1 - Embedded flash memories Technology: state of the art and trends (Part1)			Session 2 - Emerging and leading edge technologies for embedded NVM (Part 2)			Session 2 - Emerging and leading edge technologies for embedded NVM (Part 3)		
10.15 am	Dan Kochpatcharin - TSMC (The Netherlands)	"TSMC eNVM technology"	09.00 am	Sylvain Dubois - Crossbar (USA)	"Unleash new system architectures with Crossbar ReRAM for embedded applications and storage class memories"	09.00 am	Viktor Markov - SST (USA)	"ESF3 Memory: Endurance Capability and Post Cycling Data Retention."
10.40 am	Break		9.25 am	Takumi Mikawa - Panasonic / UMC (Japan)	"40nm embedded ReRAM platform in foundry with highly reliable TaOx cell technology"	9.25 am	Philippe Blanchard - Adesto Technologies (USA)	"Overview of Conductive Bridging RAM (CBRAM): an ideal NVM for IoT Applications."
11.05 am	Yasuhiro Taniguchi - Floadia (Japan)	"A new core transistor equipped with NVM functionality without using any emerging memory materials".	9.50 am	Pierre-Emmanuel Gaillardon - The University of Utah (USA)	"High-performance and Low-power Operations with RRAM-based FPGAs."	9.50 am	Gregory Di Pendina - Université Grenoble Alpes/CNRS/CEA, INAC - Spintec Lab (France)	"Spin Orbit Torque MRAM-based circuits for non-volatile logic and memories"
11.30 am	Alex Kotov - SST (USA)	"Scaling and Demonstration of a 28nm Logic-Process- Compatible Split-Gate Flash Memory Technology"	10.15 am	Hiroaki Yoda - Toshiba (Japan)	"High-speed voltage-Control spintronics memory having high-efficiency of writing, a potential of unlimited endurance, and broad design windows:"	10.15 am	Vincenzo Della Marca - IM2NP (France)	"From material to circuit : lead the embedded NVM to the next stage"
11.55 am	Weiran Kong - Huahong Grace Semiconductor (China)	A Highly Scalable Floating-Gate Cell for Embedded-Flash Applications	10.40 am	Break		10.40 am	Break	
12.20 pm	Lunch		Session 4 - Users, focus on connected objects, IoT			Session 3 - Device and architecture (Part 3)		
Session 2 - Emerging and leading edge technologies for embedded NVM (Part 1)			11.05 am	Jérôme Azémar - Yole (France)	"Emerging NVM technologies: toward mass production in MCU embedded market."	11.05 am	Gabriele Navarro - CEA, LETI, MINATEC Campus (France)	"Innovative design solutions for emerging NVM technologies"
2.00 pm	Igor Kouznetsov - Cypress Spansion (USA)	"Embedded charge-trap non-volatile memory technologies at 40-nm node and beyond"	11.30 am	Bernhard Huber - Munich University of Applied Sciences (Germany) / INRS-EMT (Canada)	"Inkjet - Printed Flexible Conductive Bridge RAM"	11.30 am	Damien Querloz - University Paris-Sud (France)	"Unconventional uses of embedded non-volatile memory: toward the "natively intelligent" memory."
2.25 pm	Gabriele Navarro - CEA, LETI, MINATEC Campus (France)	"Non-Volatile Resistive Memory: a Started Revolution Towards the Memory of the Future"	11.55 am	Franck Courbon - University of Cambridge (U.K.)	"NVM technologies: An hardware security point of view"	11.55 am	Dimitrios Rodopoulos - IMEC (Belgium)	"NVM chip for Machine Learning Operations"
2.50 pm	James Huang - eMemory (Taiwan)	"Leading logic NVM technology advancing into 7NM finfet node : Challenges and Solutions"	12.20 pm	Alexis Krakovinsky - CEA & IM2NP (France)	"Secure Characterisation of the OxRAM Technology."	12.20 pm	Lunch	
3.15 pm	Dirk Wouters - AACHEN (Germany)	"Voltage Compatibility of ReRAM operation with CMOS"	12.45 pm	Lunch / Poster session		2.00pm	End of the conference	
3.40 pm	Stefan Muller - Ferroelectric Memory Company (Germany)	"FeFET - The ideal embedded NVM for the age of IoT"	Session 3 - Device and architecture (Part 2)					
4.05 pm	Break		2.00 pm	Luca Larcher - University of Modena and Reggio Emilia (Italy)	"Multiscale Modeling of RRAM Devices for Memory and Neuromorphic Computing Applications."			
Session 3 - Device and architecture (Part 1)			2.25 pm	Virgile Javerliac - eVADERIS (France)	"Toward non-volatile digital flows."			
4.30 pm	Stephen Zhou - SMIC (China)	"SMIC Advanced eNVM Solutions For Security IOT."	2.50 pm	Marcello Traiola - LIRMM / University of Montpellier (France)	"Formal Design Space Exploration for Memristor-based Crossbar Architecture"			
4.55 pm	Yong Kyu Lee - Samsung Electronics (Korea)	"Split-Gate Flash on 28-nm HKMG Logic Process For High-Speed Embedded Secure-Element Chip Applications"	3.15 pm	Marie-Paule Besland - IMN Nantes (France)	"Resistive switching in narrow gap Mott Insulators."			
5.20 pm	Anthonin Verdy - CEA - Leti (France)	"SE-RICH GESE-BASED OTS Selector Engineering Targeting High Density Crossbar Resistive Memory."	3.40 pm	Break				
5.45 pm	End of the day		Session 1 - Embedded flash memories Technology: state of the art and trends (Part 2)					
			4.05 pm	Dann Morillon - STMicroelectronics (France)	"High and medium voltage devices integration on advanced eNVM"			
			4.30 pm	Terry Lin - eMemory (Taiwan)	"Ultra Low Power single poly non volatile memory for passive RFID applications".			
			4.55 pm	Paolo Piacentini - Kilopass (USA)	"Anti-Fuse, OTP NVM, the Only Memory Enabled at Every CMOS Process Node to 10nm Providing Code, Encryption Keys, & Confidential Data Storage."			
			5.20 pm	Tomohiro Yamashita - Renesas Electronics Corp. (Japan)	"FinFET Split-Gate MONOS for Embedded Flash in 16/14nm-node and beyond."			
			5.45 pm	End of the day				